

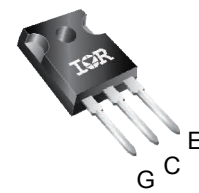
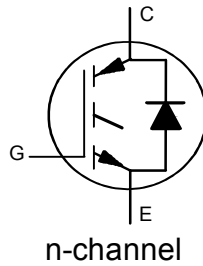
Insulated Gate Bipolar Transistor with Ultrafast Soft Recovery Diode

$$V_{CES} = 1200V$$

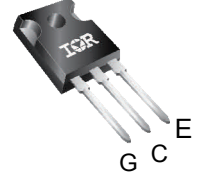
$$I_C = 15A, T_C = 100^\circ C$$

$$t_{SC} \geq 10\mu s, T_{J(max)} = 150^\circ C$$

$$V_{CE(ON)} \text{ typ.} = 1.7V @ I_C = 10A$$



IRG8P15N120KDPbF
TO-247AC



IRG8P15N120KD-EPbF
TO-247AD

G	C	E
Gate	Collector	Emitter

Applications

- Industrial Motor Drive
- UPS
- Solar Inverters
- Welding

Features	Benefits
Benchmark Low $V_{CE(ON)}$	High Efficiency in a Motor Drive Applications
10 μs Short Circuit SOA	Increases margin for short circuit protection scheme
Positive $V_{CE(ON)}$ Temperature Coefficient	Excellent Current Sharing in Parallel Operation
Square RBSOA and high I_{LM} -rating	Rugged Transient Performance
Lead-Free, RoHS compliant	Environmentally friendly

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRG8P15N120KDPbF	TO-247AC	Tube	25	IRG8P15N120KDPbF
IRG8P15N120KD-EPbF	TO-247AD	Tube	25	IRG8P15N120KD-EPbF

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current (Silicon Limited)	30	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	15	
I_{CM}	Pulse Collector Current (see fig. 2)	30	
I_{LM}	Clamped Inductive Load Current (see fig. 3)①	40	
$I_F @ T_C = 25^\circ C$	Diode Continuous Forward Current	20	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	11	V
I_{FM}	Diode Maximum Forward Current ⑤	40	
V_{GE}	Continuous Gate-to-Emitter Voltage	± 30	V
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	125	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	50	
T_J	Operating Junction and	-40 to +150	C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw	10 lbf·in (1.1 N·m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case-(each IGBT) ②	—	—	1.0	$^\circ C/W$
$R_{\theta JC}$ (Diode)	Thermal Resistance Junction-to-Case-(each Diode) ②	—	—	1.7	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	—	0.24	—	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (typical socket mount)	—	40	—	

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$ ③
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	1.1	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1mA$ (25 $^\circ\text{C}$ -150 $^\circ\text{C}$)
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.7	2.0	V	$I_C = 10A, V_{GE} = 15V, T_J = 25^\circ\text{C}$
		—	2.0	—		$I_C = 10A, V_{GE} = 15V, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	5.0	—	6.5	V	$V_{CE} = V_{GE}, I_C = 400\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage Temperature Coeff.	—	-16	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 400\mu A$ (25 $^\circ\text{C}$ -150 $^\circ\text{C}$)
g_{fe}	Forward Transconductance	—	5.7	—	S	$V_{CE} = 50V, I_C = 10A, PW = 20\mu s$
I_{CES}	Collector-to-Emitter Leakage Current	—	1.0	30	μA	$V_{GE} = 0V, V_{CE} = 1200V$
		—	1.0	—	mA	$V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 30V$
V_F	Diode Forward Voltage Drop	—	2.1	2.7	V	$I_F = 10A$
		—	2.4	—		$I_F = 10A, T_J = 150^\circ\text{C}$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max④	Units	Conditions
Q _g	Total Gate Charge (turn-on)	—	65	98	nC	I _C = 10A
Q _{ge}	Gate-to-Emitter Charge (turn-on)	—	6.0	9.0		V _{GE} = 15V
Q _{gc}	Gate-to-Collector Charge (turn-on)	—	40	60		V _{CC} = 600V
E _{on}	Turn-On Switching Loss	—	0.6	—	mJ	I _C = 10A, V _{CC} = 600V, V _{GE} =15V R _G = 10Ω, T _J = 25°C
E _{off}	Turn-Off Switching Loss	—	0.6	—		
E _{total}	Total Switching Loss	—	1.2	—		
t _{d(on)}	Turn-On delay time	—	15	—	ns	Energy losses include tail & diode reverse recovery ⑥
t _r	Rise time	—	20	—		
t _{d(off)}	Turn-Off delay time	—	170	—		
t _f	Fall time	—	200	—	mJ	I _C = 10A, V _{CC} = 600V, V _{GE} =15V R _G = 10Ω, T _J = 150°C
E _{on}	Turn-On Switching Loss	—	0.9	—		
E _{off}	Turn-Off Switching Loss	—	1.1	—		
E _{total}	Total Switching Loss	—	2.0	—	ns	Energy losses include tail & diode reverse recovery ⑥
t _{d(on)}	Turn-On delay time	—	15	—		
t _r	Rise time	—	20	—		
t _{d(off)}	Turn-Off delay time	—	250	—	pF	V _{GE} = 0V V _{CC} = 30V f = 1.0Mhz
t _f	Fall time	—	330	—		
C _{ies}	Input Capacitance	—	1290	—		
C _{oes}	Output Capacitance	—	60	—	—	T _J = 150°C, I _C = 40A V _{CC} = 960V, V _p ≤ 1200V V _{GE} = +20V to 0V
C _{res}	Reverse Transfer Capacitance	—	30	—		
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				
SCSOA	Short Circuit Safe Operating Area	10	—	—	μs	T _J = 150°C, V _{CC} = 600V, V _p ≤ 1200V V _{GE} = +15V to 0V
E _{rec}	Reverse Recovery Energy of the Diode	—	0.8	—	mJ	T _J = 150°C
t _{rr}	Diode Reverse Recovery Time	—	60	—	ns	V _{CC} = 600V, I _F = 10A
I _{rr}	Peak Reverse Recovery Current	—	26	—	A	V _{GE} = 15V, R _g = 10Ω

Notes:

- ① $V_{CC} = 80\% (V_{CES}), V_{GE} = 20V$.
- ② R_θ is measured at T_J of approximately 90 $^\circ\text{C}$.
- ③ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.
- ④ Maximum limits are based on statistical sample size characterization.
- ⑤ Pulse width limited by max. junction temperature.
- ⑥ Values influenced by parasitic L and C in measurement.

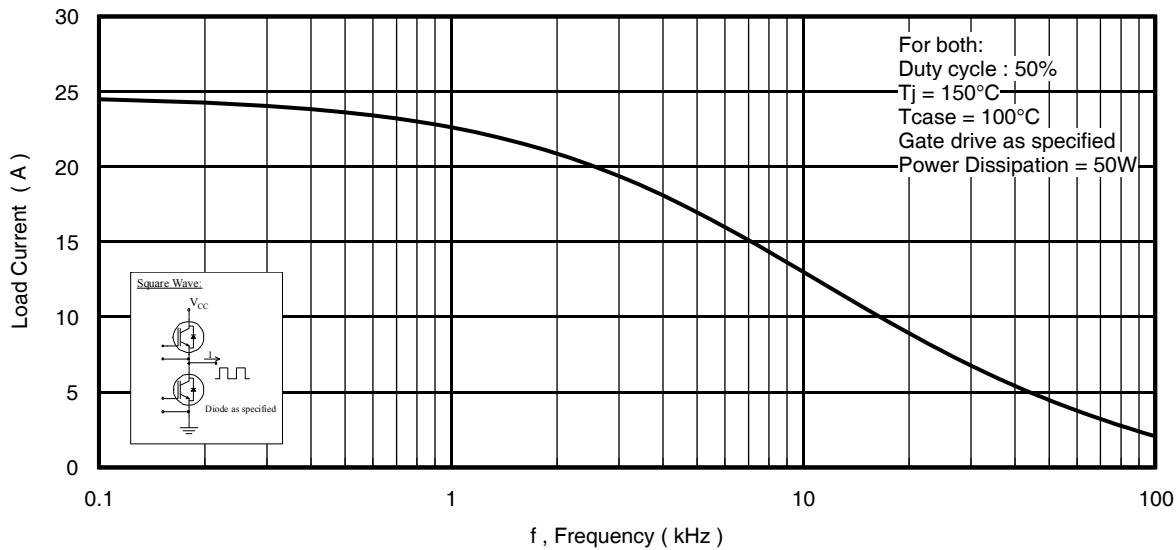


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

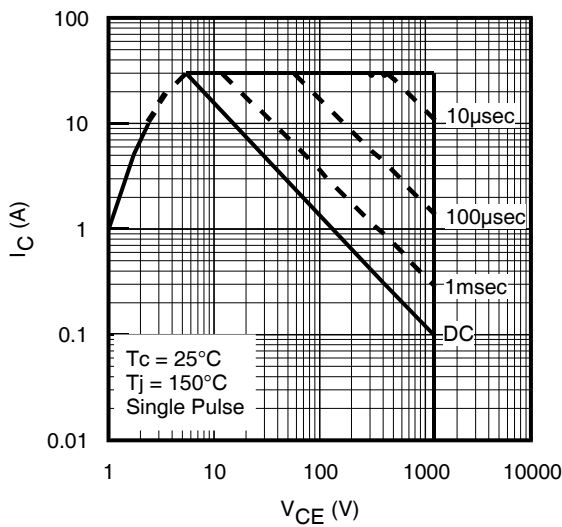


Fig. 2 - Forward SOA

$T_c = 25^{\circ}\text{C}$; $T_j \leq 150^{\circ}\text{C}$; $V_{\text{GE}} = 15\text{V}$

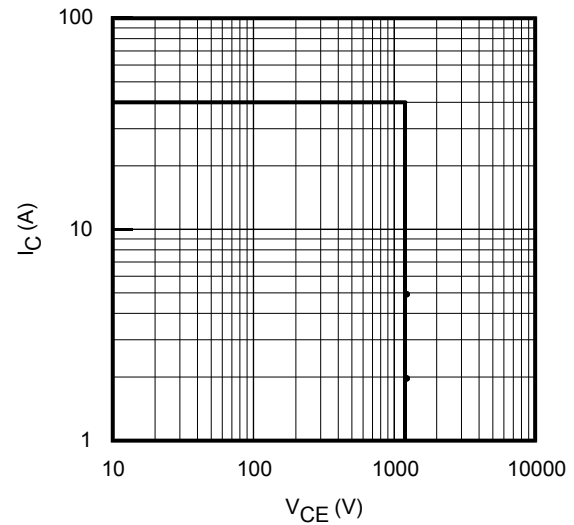


Fig. 3 - Reverse Bias SOA

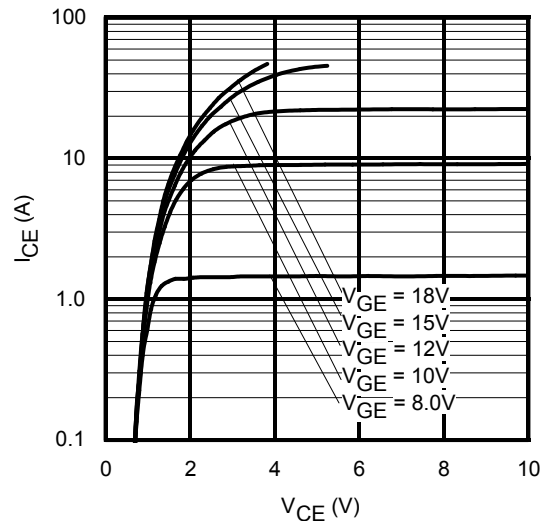


Fig. 4 - Typ. IGBT Output Characteristics
 $T_j = 25^{\circ}\text{C}$; $t_p = 20\mu\text{s}$

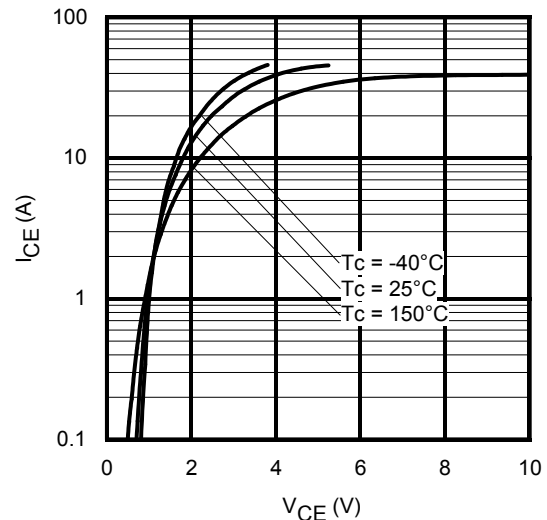


Fig. 5 - Typ. IGBT Saturation Voltage
 $V_{\text{GE}} = 15\text{V}$; $t_p = 20\mu\text{s}$

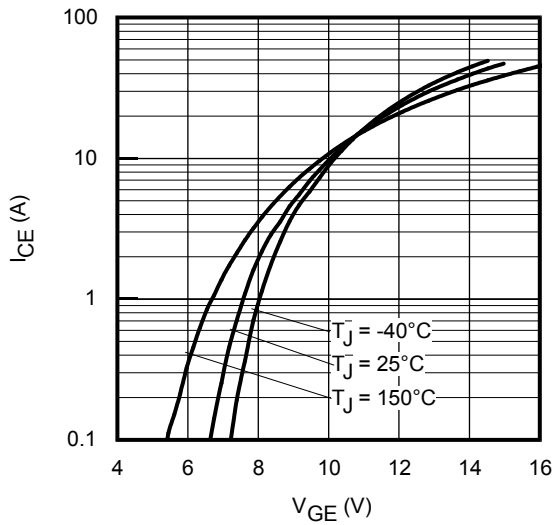


Fig. 6 - Typ. Transfer Characteristics
 $V_{CE} = 50V$; $t_p = 20\mu s$

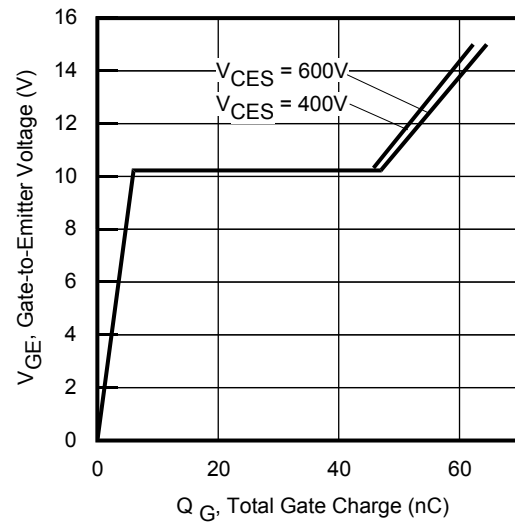


Fig. 7 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 10A$

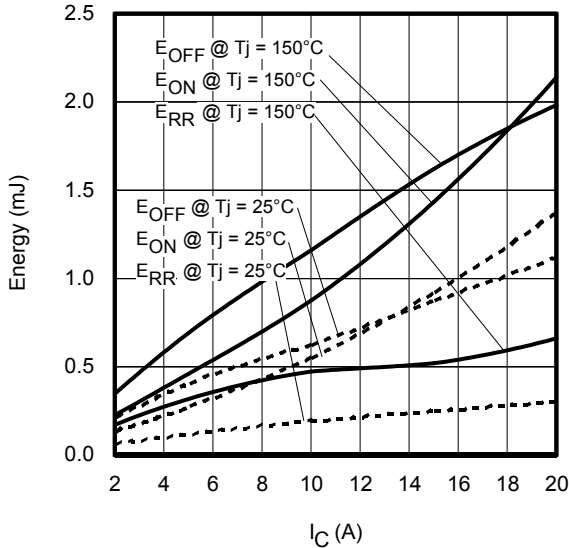


Fig. 8 - Typ. Energy Loss vs. I_C
 $V_{CE} = 600V$, $R_G = 10\Omega$; $V_{GE} = 15V$

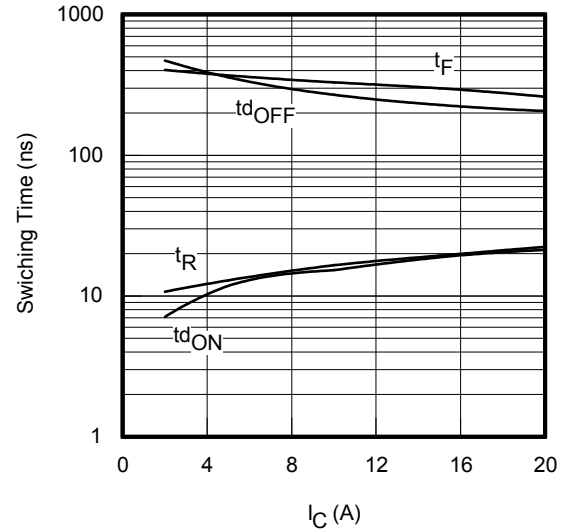


Fig. 9 - Typ. Switching Time vs. I_C
 $T_J = 150^\circ C$; $V_{CE} = 600V$, $R_G = 10\Omega$; $V_{GE} = 15V$

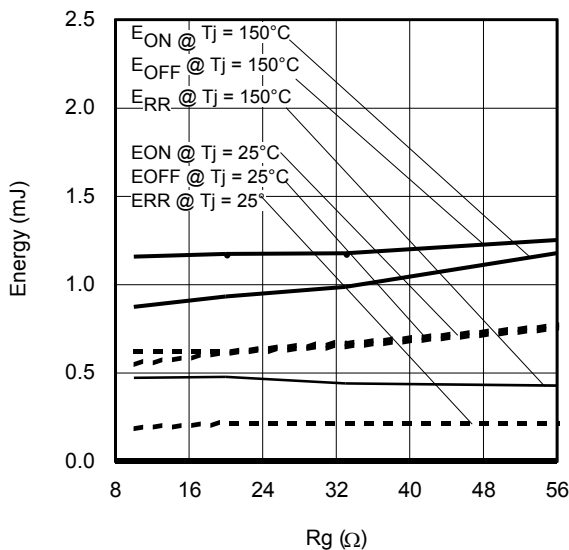


Fig. 10 - Typ. Energy Loss vs. R_G
 $V_{CE} = 600V$, $I_{CE} = 10A$; $V_{GE} = 15V$

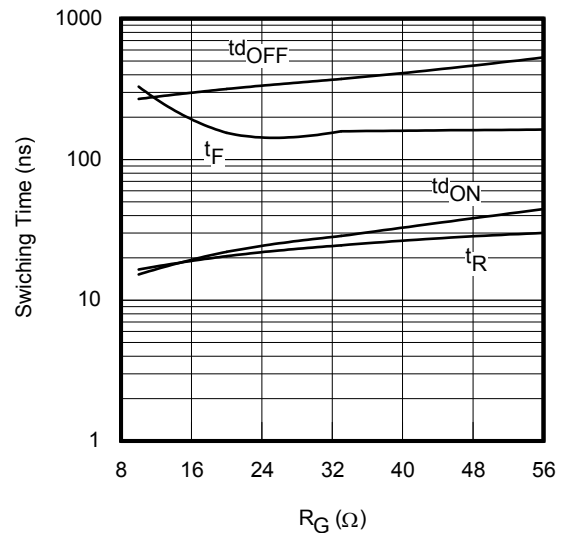


Fig. 11 - Typ. Switching Time vs. R_G
 $T_J = 150^\circ C$; $V_{CE} = 600V$, $I_{CE} = 10A$; $V_{GE} = 15V$

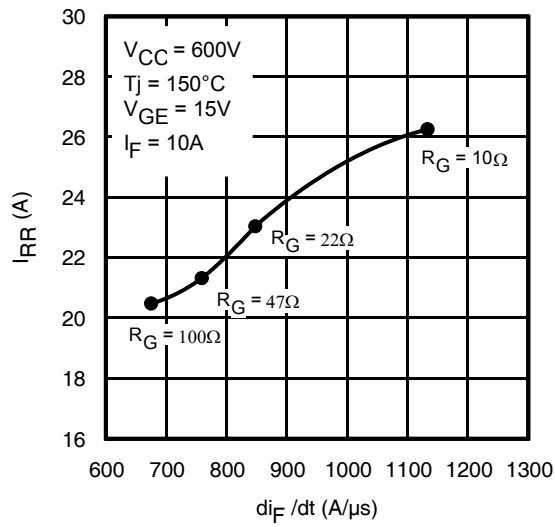


Fig. 12 - Typ. I_{RR} vs. di/dt

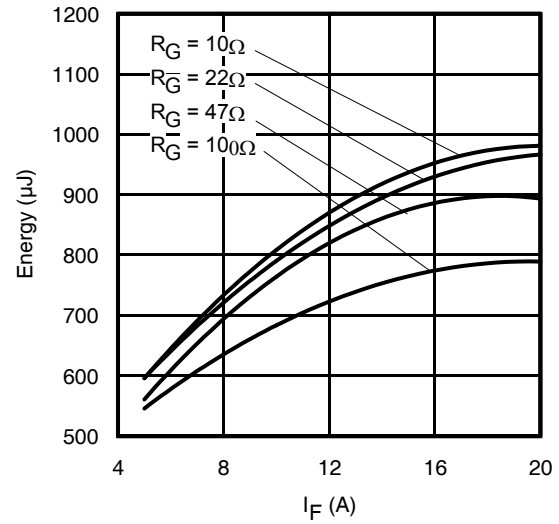


Fig. 13 - Typ. Diode E_{RR} vs. I_F
 $T_J = 150^\circ\text{C}$

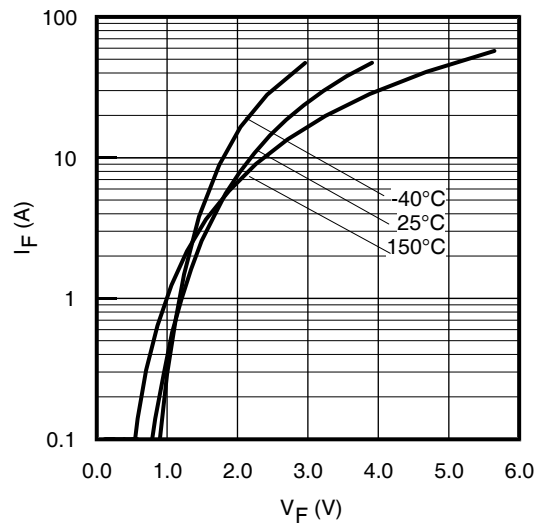


Fig. 14 - Typ. Diode Forward Voltage Drop Characteristics

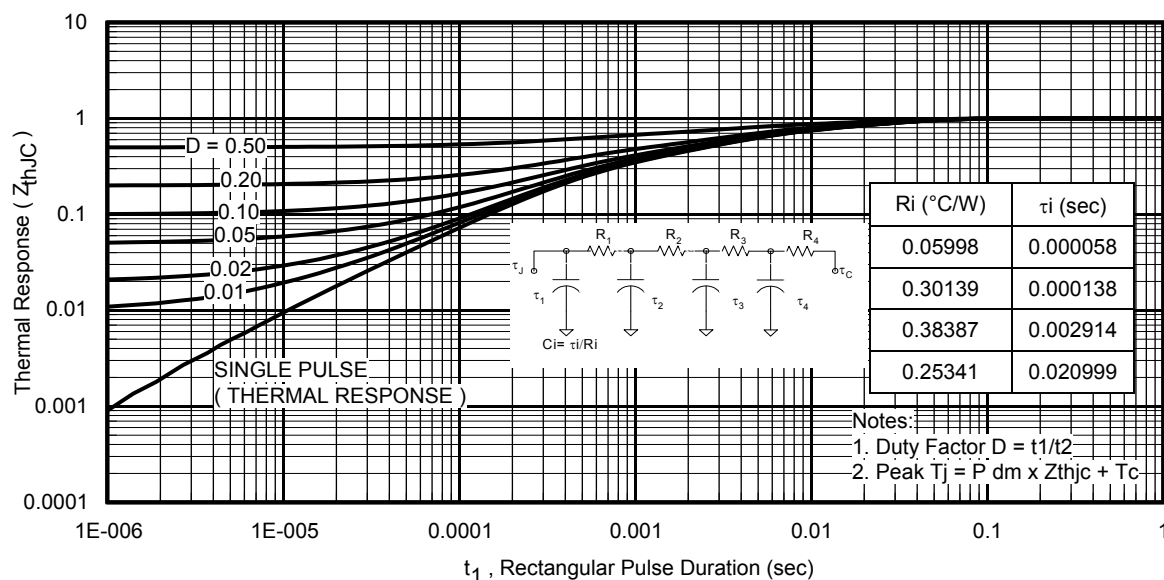


Fig. 15 - Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

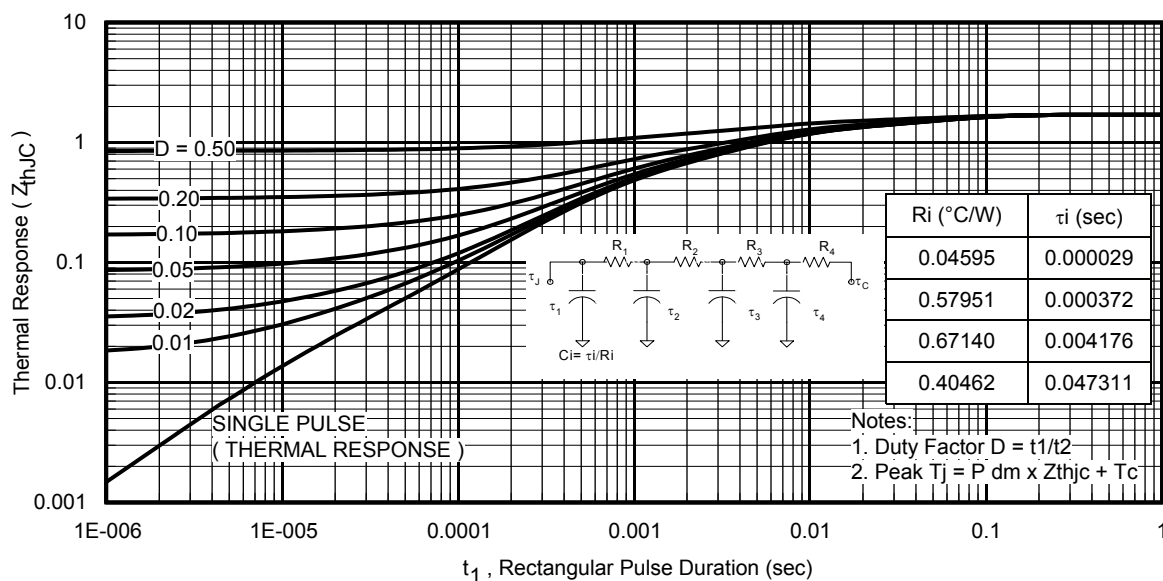
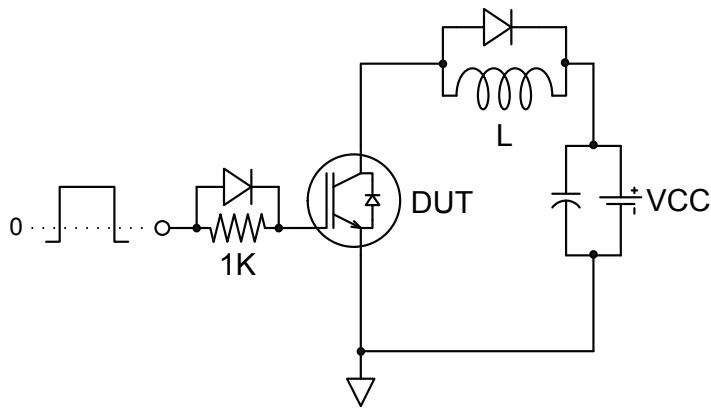
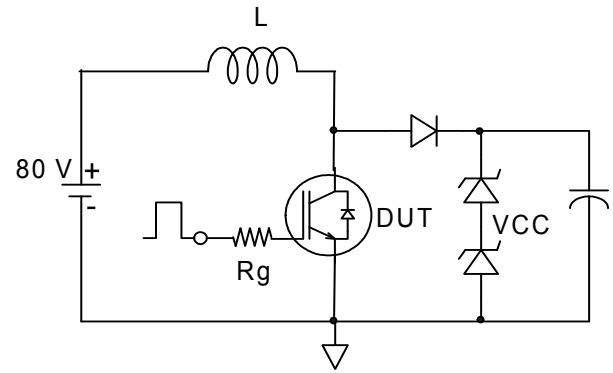
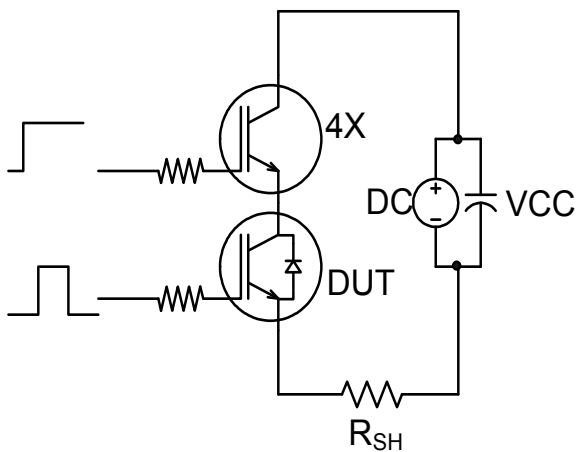
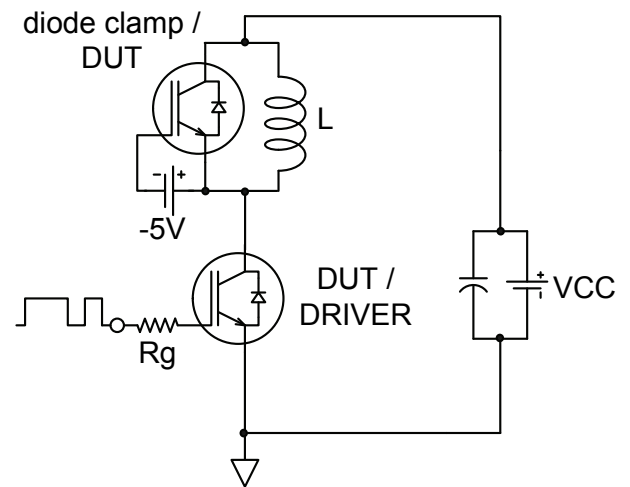
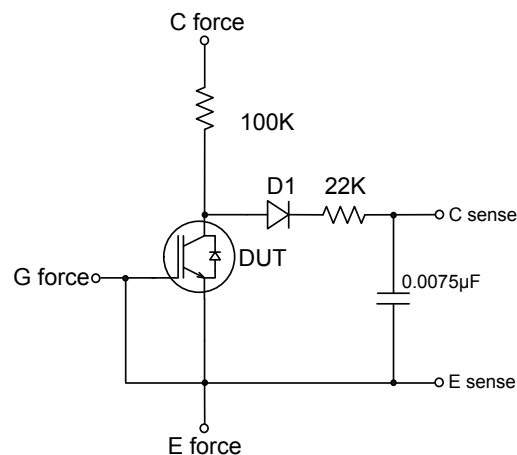


Fig. 16 - Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)


Fig.C.T.1 - Gate Charge Circuit (turn-off)

Fig.C.T.2 - RBSOA Circuit

Fig.C.T.3 - S.C. SOA Circuit

Fig.C.T.4 - Switching Loss Circuit
(Board Stray Inductance 180nH)

Fig.C.T.5 - BVCES Filter Circuit

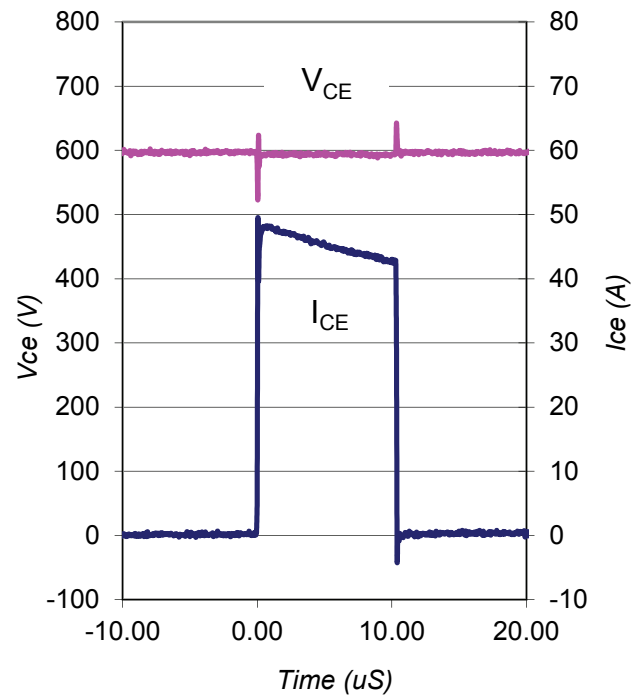
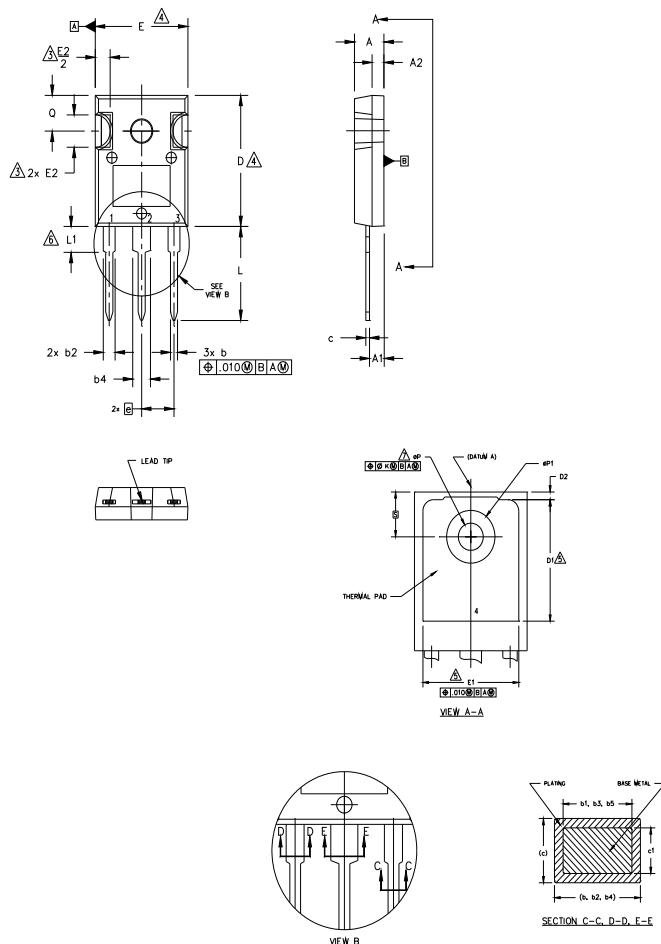


Fig. WF4 - Typ. S.C. Waveform
@ $T_J = 150^{\circ}\text{C}$ using Fig. CT.3

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	—	13.08	—	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	—	13.46	—	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
ØP	.140	.144	3.56	3.66	
ØP1	—	.291	—	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

DIODES

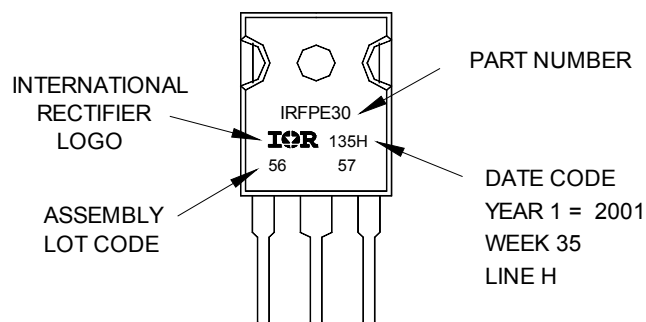
- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AC Part Marking Information

Notes: This part marking information applies to devices produced after 02/26/2001

EXAMPLE: THIS IS AN IRFPE30
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2001
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position indicates "Lead-Free"

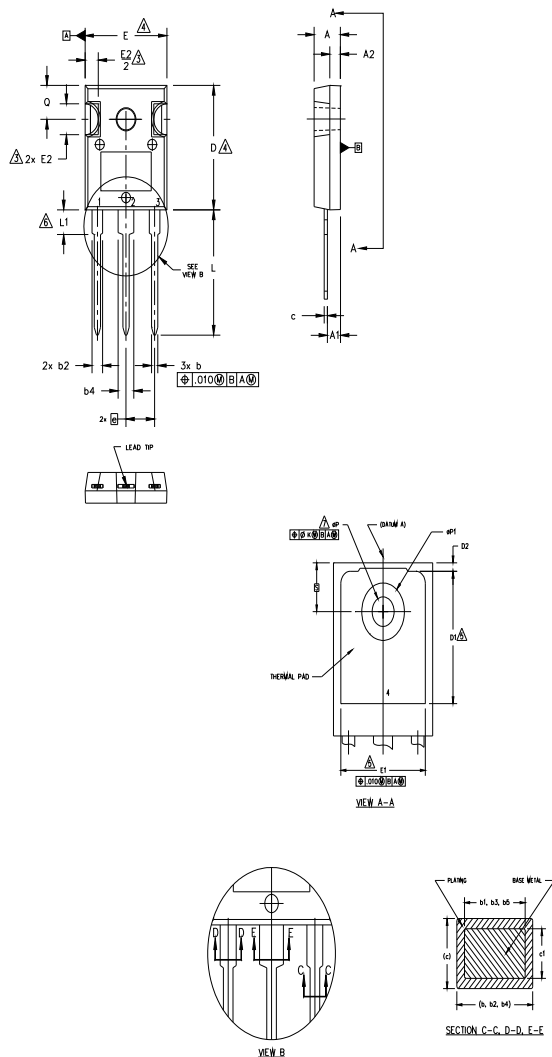


TO-247AC package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

TO-247AD Package Outline

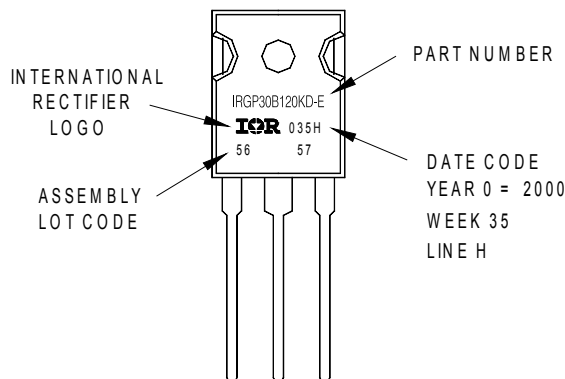
Dimensions are shown in millimeters (inches)



TO-247AD Part Marking Information

EXAMPLE: THIS IS AN IRGP30B120KD-E
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position indicates "Lead-Free"



TO-247AD package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information[†]

Qualification Level	Industrial [†] (per JEDEC JESD47F) ^{††}	
Moisture Sensitivity Level	TO-247AC	N/A
	TO-247AD	N/A
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability/>

†† Applicable version of JEDEC standard at the time of product release.

International
 Rectifier

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To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>